

## **isc Silicon PNP Power Transistors**

# BD376/378/380

### **DESCRIPTION**

- DC Current Gain-
- : h<sub>FE</sub>= 20(Min)@ I<sub>C</sub>= -1A
- Complement to Type BD375/377/379
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

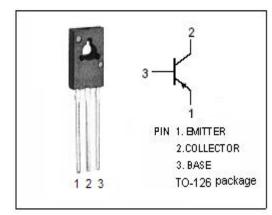
### **APPLICATIONS**

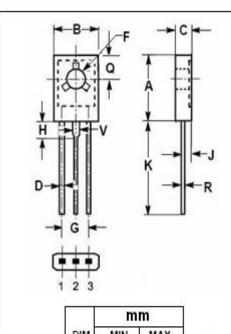
Designed for medium power linear and switching applications



## ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25℃)

SYMBOL	PARAMETER	1	VALUE	UNIT	
		BD376	-50	V	
$V_{\text{CBO}}$	Collector-Base Voltage	BD378	-75		
		BD380	-100		
	0. 64	BD376	-45		
V <sub>CEO</sub>	Collector-Emitter Voltage	BD378	-60	٧	
		BD380	-80		
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V		
Ic	Collector Current-Continuo	-2	Α		
Ісм	Collector Current-Peak	-3	Α		
I <sub>B</sub>	Base Current-Continuous	-1	Α		
Pc	Collector Power Dissipatio @ T <sub>C</sub> =25°C	25	W		
Тл	Junction Temperature	150	$^{\circ}$ C		
T <sub>stg</sub>	Storage Temperature Ran	-55~150	°C		





	mm			
DIM	MIN	MAX		
Α	10.70	10.95		
В	7.70	7.90		
C	2.60	2.80		
D	0.66	0.86		
F	3.10	3.30		
G	4.48	4.68		
Н	2.00	2.20		
J	1.35	1.55		
K	15.30	16.30		
Q	3.70	3.90		
R	0.40	0.60		
٧	1.17	1.37		



# isc Silicon PNP Power Transistors

BD376/378/380

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	BD376	I <sub>C</sub> = -30mA ; I <sub>B</sub> = 0	-45			
		BD378		-60			V
		BD380		-80			
	Collector-Base Voltage	BD376		-50			
V <sub>СВО</sub>		BD378	I <sub>C</sub> = -0.1mA ; I <sub>E</sub> = 0	-75			V
		BD380		-100			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage		I <sub>C</sub> = -1A; I <sub>B</sub> = -0.1A			-1.0	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage		I <sub>C</sub> = -1A; V <sub>CE</sub> = -2V			-1.5	V
	Collector Cutoff Current	BD376	V <sub>CB</sub> = -45V; I <sub>E</sub> = 0			-2	
Ісво		BD378	V <sub>CB</sub> = -60V; I <sub>E</sub> = 0			-2	μ <b>Α</b>
		BD380	V <sub>CB</sub> = -80V; I <sub>E</sub> = 0			-2	
I <sub>EBO</sub>	Emitter Cutoff Current		V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-0.1	mA
h <sub>FE-1</sub>	DC Current Gain		I <sub>C</sub> = -0.15A ; V <sub>CE</sub> = -2V	40		375	
h <sub>FE-2</sub>	DC Current Gain		I <sub>C</sub> = -1A; V <sub>CE</sub> = -2V	20			
Switching Times							
t <sub>on</sub>	Turn-On Time		I <sub>C</sub> = -0.5A; I <sub>B1</sub> = -I <sub>B2</sub> = -50mA;		0.05		μs
t <sub>off</sub>	Turn-Off Time	11	V <sub>CC</sub> = -30V		0.5		μs

### ♦ h<sub>FE-1</sub> Classifications

6	10	16	25
40-100	63-160	100-250	150-375

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